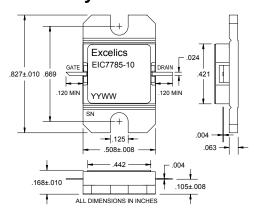
# **EIC7785-10**

**UPDATED 04/12/2006** 

## 7.70-8.50 GHz 10-Watt Internally Matched Power FET

### **FEATURES**

- 7.70-8.50GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +40.5 dBm Output Power at 1dB Compression
- 8.5 dB Power Gain at 1dB Compression
- 28% Power Added Efficiency
- -46 dBc IM3 at PO = 29.5 dBm SCL
- **Hermetic Metal Flange Package**
- 100% Tested for DC, RF, and R<sub>TH</sub>



## **ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25°C)**



## Caution! ESD sensitive device.

SYMBOL	PARAMETERS/TEST CONDITIONS <sup>1</sup>	MIN	TYP	MAX	UNITS
P <sub>1dB</sub>	Output Power at 1dB Compression $f = 7.70-8.50GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 3200\text{mA}$	39.5	40.5		dBm
G <sub>1dB</sub>	Gain at 1dB Compression $f = 7.70-8.50GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 3200\text{mA}$	7.5	8.5		dB
ΔG	Gain Flatness $f = 7.70-8.50GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 3200\text{mA}$			±0.6	dB
PAE	Power Added Efficiency at 1dB Compression $V_{DS}$ = 10 V, $I_{DSQ} \approx 3200$ mA f = 7.70-8.50GHz		28		%
Id <sub>1dB</sub>	Drain Current at 1dB Compression f = 7.70-8.50GHz		3300	3700	mA
IM3	Output 3rd Order Intermodulation Distortion $\Delta f = 10$ MHz 2-Tone Test; Pout = 29.5 dBm S.C.L <sup>2</sup> $V_{DS} = 10$ V, $I_{DSQ} \approx 65\%$ IDSS $f = 8.50$ GHz		-46		dBc
I <sub>DSS</sub>	Saturated Drain Current V <sub>DS</sub> = 3 V, V <sub>GS</sub> = 0 V		5700	7100	mA
V <sub>P</sub>	Pinch-off Voltage V <sub>DS</sub> = 3 V, I <sub>DS</sub> = 57 mA		-2.5	-4.0	V
R <sub>TH</sub>	Thermal Resistance <sup>3</sup>		2.5	3.0	°C/W

Note: 1) Tested with 50 Ohm gate resistor.

2) S.C.L. = Single Carrier Level.

3) Overall Rth depends on case mounting.

### ABSOLUTE MAXIMUM RATING<sup>1,2</sup>

SYMBOLS	PARAMETERS	ABSOLUTE <sup>1</sup>	CONTINUOUS <sup>2</sup>
Vds	Drain-Source Voltage	15	10V
Vgs	Gate-Source Voltage	-5	-4V
lgsf	Forward Gate Current	104.4mA	34.8mA
lgsr	Reserve Gate Current	-17.4mA	-5.8mA
Pin	Input Power	39.5dBm	@ 3dB Compression
Tch	Channel Temperature	175 °C	175 °C
Tstg	Storage Temperature	-65 to +175 °C	-65 to +175 °C
Pt	Total Power Dissipation	50W	50W

Note: 1. Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.